

# 30A 60V SchottkyBarrierDiode

## 1 Description

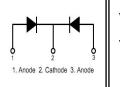
Dual center tab Schottky rectifier suited for High Frequency server and telecom base station SMPS. Packaged in TO, this device combines high current rating and low volume to enhance both reliability and power density of the application.

#### 2 Features

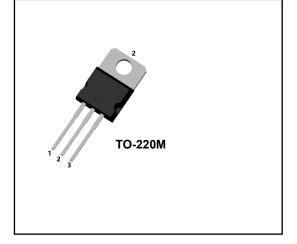
- High junction temperature capabiliy
- Low leakage current
- Low thermal resistance
- High frequency operation
- Avalanche specification

## 3 Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose



 $V_{BR}$  = 60V  $V_{F(single)(Max)}$  = 0.80V  $I_{F(AV)(single)}$  = 15A



#### 4 Electrical Characteristics

## **4.1 Absolute Maximum Ratings** (Tc=25 °C,unless otherwise noted)

| PARAMETER                                 |          | SYM               | BOL            | VALUE   | UNIT                 |
|---|----------|-------------------|----------------|---------|----------------------|
| Peak Repetitive Reverse Voltage           |          | VF                | RRM            | 60      | V                    |
| RMS Reverse Voltage                       |          | V <sub>R(</sub>   | RMS)           | 48      | V                    |
| DC Blocking Voltage                       |          |                   | / <sub>R</sub> | 60      | V                    |
| Average Rectified Forward Current(single) | Tc=120°C |                   |                |         | А                    |
| Average Rectified Forward Current(double) |          | I <sub>F</sub> (  | (AV)           | 30      | А                    |
| Repetitive Peak Surge Current(single)     |          | IF                | RM             | 20      | А                    |
| Nonrepetitive Peak Surge Current(single)  | t=8.3r   | ns I <sub>F</sub> | SM             | 250     | А                    |
| Avalanche Energy(single)                  | L=1m     | Н Е               | AS             | 15      | mJ                   |
| Operating Junction Temperature Range      | ·        | -                 | Гј             | -55~150 | $^{\circ}\mathbb{C}$ |
| Storage Temperature Range                 |          |                   | stg            | -55~150 | $^{\circ}$ C         |
| ESD (Machine Model=C)                     |          |                   |                | >400    | V                    |
| ESD (Human Body Model=3B)                 |          |                   |                | >8000   | V                    |
| ESD(Noncontact)                           |          |                   |                | >15000  | V                    |

### 4.2 Thermal Characteristics

| PARAMETER                                 | SYMBOL            | VALUE | UNIT |
|---|-------------------|-------|------|
| Thermal Resistance, Junction to Case-sink | R <sub>thJC</sub> | 2.0   | °C/W |



### 4.3 Electrical Characteristics

(Tc=25<sup>°</sup>C,unless otherwise noted)

| PARAMETER             | SYMBOL         | TEST CONDITION                              | MIN | TYP  | MAX  | UNIT |
|-----------------------|----------------|---|-----|------|------|------|
| Maximum Instantaneous |                | I <sub>F</sub> = 15A                        | -   | 0.71 | 0.80 | V    |
| Forward Voltage       | V <sub>F</sub> | I <sub>F</sub> = 15A, T <sub>C</sub> = 125℃ | -   | 0.60 | -    | V    |
|                       |                | I <sub>F</sub> = 20A                        | -   | 0.79 | 0.85 | V    |
|                       |                | I <sub>F</sub> = 30A                        |     | 0.83 | 0.90 | V    |
| Maximum Instantaneous | I <sub>R</sub> | V <sub>R</sub> = 60V                        | -   | 10   | 50   | uA   |
| Reverse               |                | V <sub>R</sub> = 60V, TC = 125°C            | -   | -    | 20   | mA   |
| Total capacitance     | Ctot           | V <sub>R</sub> =0V f=1MHz                   | -   | 180  | -    | pF   |
| DC Blocking Voltage   | $V_{BR}$       | I <sub>R</sub> =100uA                       | 60  | 71   | -    | V    |

DEFINITIONS

VF = Instantaneous forward voltage (pw =  $300\mu s$ , D = 2%).

IR = Instantaneous reverse current.

RθJC = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

# 5 Typical characteristics diagrams

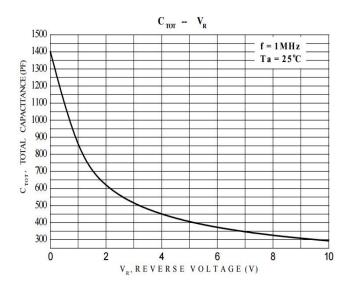


FIGURE 1. Total capacitance vs Voltage

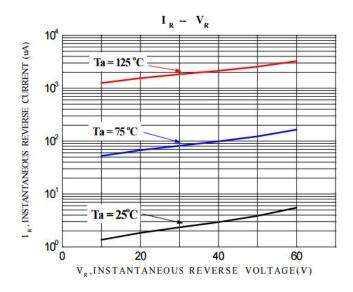
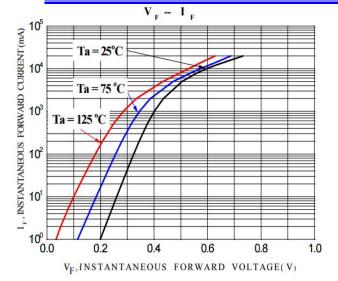


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE







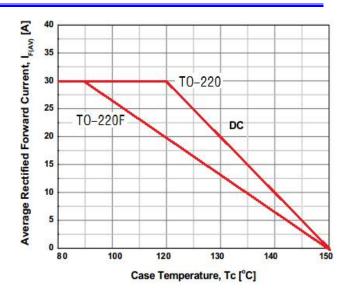


FIGURE 4. CURRENT DERATING CURVE

# 6 Typical Test Circuit and Waveform

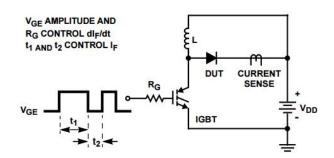


FIGURE 5. trr TEST CIRCUIT

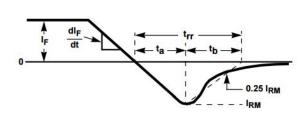


FIGURE 6. trr WAVEFORMS AND DEFINITIONS

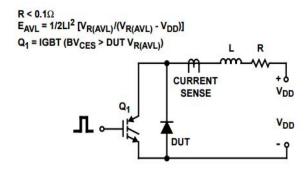


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

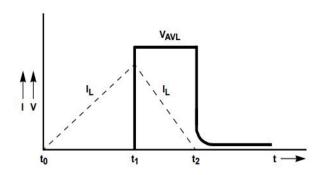


FIGURE8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

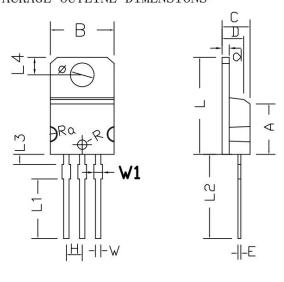


7 Product Specifications and Packaging Models

| Product Model | Package Type | Mark Name | RoHS    | Package | Quantity |
|---------------|--------------|-----------|---------|---------|----------|
| MBR3060CT     | TO-220       | MBR3060CT | Pb-free | Tube    | 1000/box |

### 8 Dimensions

### TO-220M PACKAGE OUTLINE DIMENSIONS



| Cambo 1 | Dimensions 1 | In Millimeters | Dimensions | In Inches |
|---------|--------------|----------------|------------|-----------|
| Symbol  | min.         | max.           | min.       | max.      |
|         | MIN          | MAX            | MIN        | MAX       |
| A       | 7. 55        | 8.05           | 0. 297     | 0.317     |
| В       | 9.85         | 10. 25         | 0. 388     | 0.404     |
| С       | 4. 20        | 4.80           | 0. 165     | 0. 189    |
| D       | 3. 20        | 3.60           | 0. 126     | 0.142     |
| E       | 0.42         | 0.47           | 0.017      | 0.019     |
| L       | 15. 20       | 15.60          | 0. 598     | 0.614     |
| Н       | 2. 52        | 2.56           | 0.099      | 0. 101    |
| W       | 0.78         | 0.88           | 0.031      | 0.035     |
| Φ       | 3.60         | 3.90           | 0.142      | 0. 154    |
| R       | 0.72         | 0.78           | 0.028      | 0.031     |
| Ra      | 9.00         | 10. 5          | 0.354      | 0.413     |
| d       | 1. 10        | 1.40           | 0.043      | 0.055     |
| L1      | 9. 3         | 9.7            | 0.366      | 0.382     |
| L2      | 13.00        | 13.60          | 0. 512     | 0. 535    |
| L3      | 1. 20        | 1.70           | 0.047      | 0.067     |
| L4      | 2. 60        | 3.0            | 0. 102     | 0.118     |
| W1      | 1. 10        | 1.50           | 0.043      | 0.059     |

#### 9 Attentions

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- Product promotion is endless, our company will be dedicated to provide customers with better products.

### 10 Appendix

## Revision history:

| Date       | REV. | Description               | Page  |
|------------|------|---------------------------|-------|
| 2023.1.6   | 1.0  | Original                  |       |
| 2023.10.27 | 1.1  | Modify product parameters | 2Page |